



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



4-Mbit (128K × 36) Pipelined Sync SRAM

Features

- Fully registered inputs and outputs for pipelined operation
- 128K × 36 common I/O architecture
- 3.3 V core power supply (V_{DD})
- 2.5- / 3.3-V I/O power supply (V_{DDQ})
- Fast clock to output times: 2.6 ns (for 250 MHz device)
- User selectable burst counter supporting Intel Pentium interleaved or linear burst sequences
- Separate processor and controller address strobes
- Synchronous self timed writes
- Asynchronous output enable
- Offered in Pb-free 100-pin TQFP package
- “ZZ” sleep mode option and stop clock option
- Available in commercial and industrial temperature range

Functional Description

The CY7C1347G is a 3.3 V, 128K × 36 synchronous pipelined SRAM designed to support zero-wait-state secondary cache with minimal glue logic. CY7C1347G I/O pins can operate at either the 2.5 V or the 3.3 V level. The I/O pins are 3.3 V tolerant when $V_{DDQ} = 2.5$ V. All synchronous inputs pass through input registers controlled by the rising edge of the clock. All data outputs pass through output registers controlled by the rising edge of the clock. Maximum access delay from the clock rise is 2.6 ns (250 MHz device). CY7C1347G supports either the interleaved burst sequence used by the Intel Pentium processor or a linear burst sequence used by processors such as the PowerPC. The burst sequence is selected through the MODE pin. Accesses can be initiated by asserting either the address strobe from processor (\overline{ADSP}) or the address strobe from controller (\overline{ADSC}) at clock rise. Address advancement through the burst sequence is controlled by the ADV input. A 2-bit on-chip wraparound burst counter captures the first address in a burst sequence and automatically increments the address for the rest of the burst access.

Byte write operations are qualified with the four Byte Write Select ($BW_{[A:D]}$) inputs. A global write enable (\overline{GW}) overrides all byte write inputs and writes data to all four bytes. All writes are conducted with on-chip synchronous self timed write circuitry.

Three synchronous chip Selects ($\overline{CE}_1, CE_2, \overline{CE}_3$) and an asynchronous output enable (\overline{OE}) provide for easy bank selection and output tristate control. To provide proper data during depth expansion, \overline{OE} is masked during the first clock of a read cycle when emerging from a deselected state.

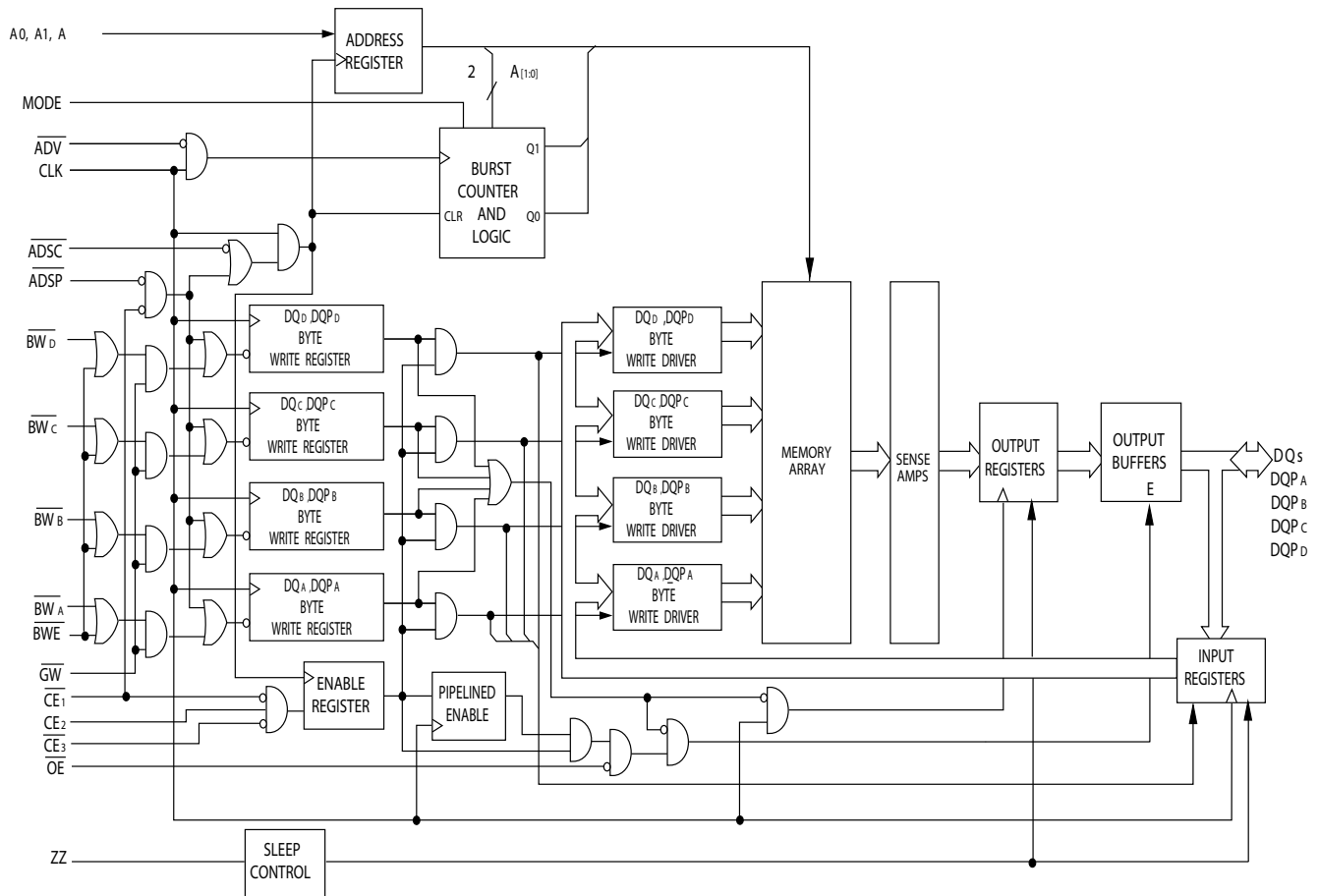
For a complete list of related documentation, click [here](#).

Selection Guide

| Description | 250 MHz | 200 MHz | 166 MHz | 133 MHz | Unit |
|------------------------------|---------|---------|---------|---------|------|
| Maximum access time | 2.6 | 2.8 | 3.5 | 4.0 | ns |
| Maximum operating current | 325 | 265 | 240 | 225 | mA |
| Maximum CMOS standby current | 40 | 40 | 40 | 40 | mA |

Errata: For information on silicon errata, see "Errata" on page 22. Details include trigger conditions, devices affected, and proposed workaround.

Logic Block Diagram

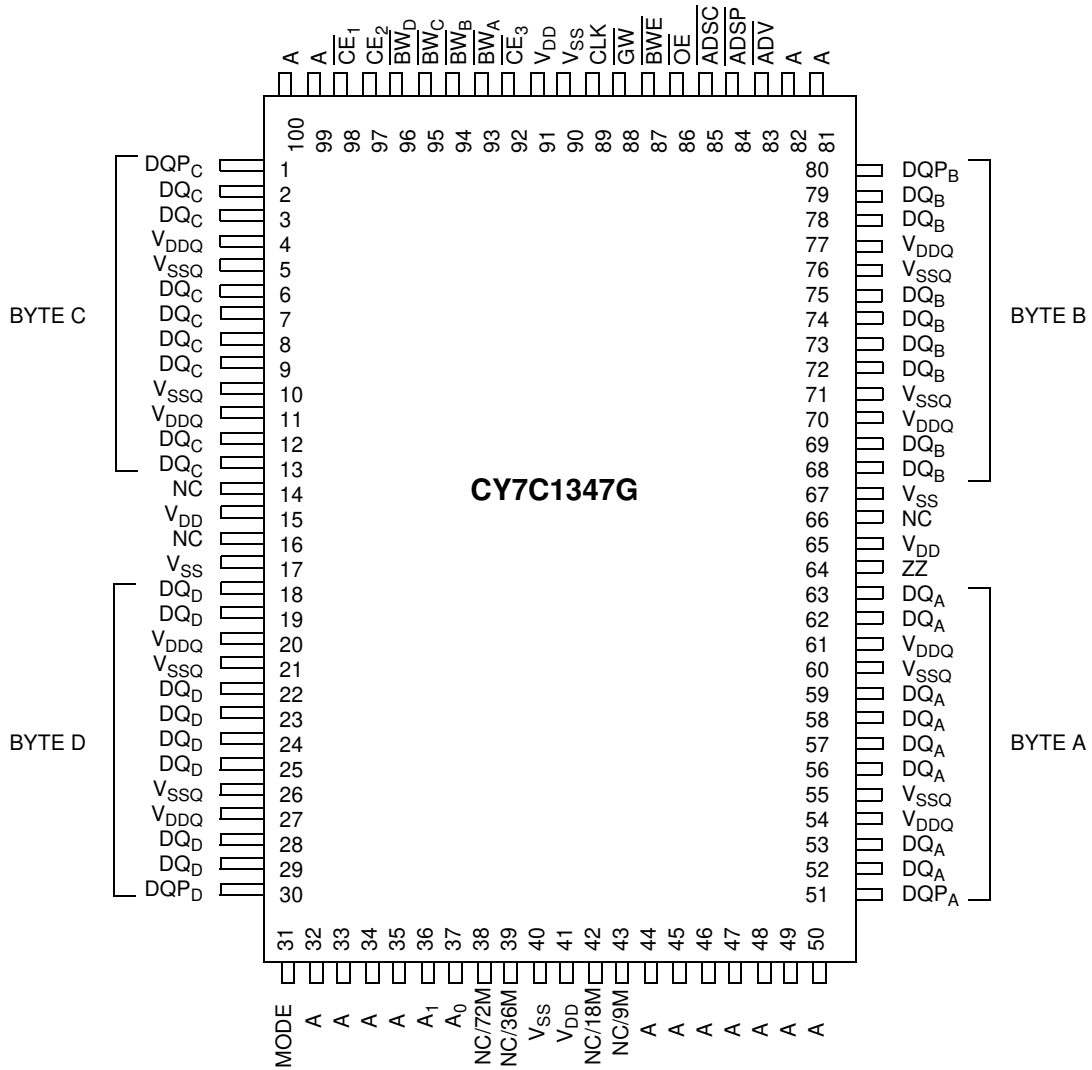


Contents

| | | | |
|---|-----------|--|-----------|
| Pin Configurations | 4 | Switching Characteristics | 14 |
| Pin Definitions | 5 | Switching Waveforms | 15 |
| Functional Overview | 7 | Ordering Information | 19 |
| Single Read Accesses | 7 | Ordering Code Definitions | 19 |
| Single Write Accesses Initiated by ADSP | 7 | Package Diagrams | 20 |
| Single Write Accesses Initiated by ADSC | 7 | Acronyms | 21 |
| Burst Sequences | 7 | Document Conventions | 21 |
| Sleep Mode | 8 | Units of Measure | 21 |
| Interleaved Burst Sequence | 8 | Errata | 22 |
| Linear Burst Sequence | 8 | Part Numbers Affected | 22 |
| ZZ Mode Electrical Characteristics | 8 | Product Status | 22 |
| Truth Table | 9 | Ram9 Sync ZZ Pin Issues Errata Summary | 22 |
| Partial Truth Table for Read/Write | 10 | Document History Page | 23 |
| Maximum Ratings | 11 | Sales, Solutions, and Legal Information | 25 |
| Operating Range | 11 | Worldwide Sales and Design Support | 25 |
| Neutron Soft Error Immunity | 11 | Products | 25 |
| Electrical Characteristics | 11 | PSoC@Solutions | 25 |
| Capacitance | 13 | Cypress Developer Community | 25 |
| Thermal Resistance | 13 | Technical Support | 25 |
| AC Test Loads and Waveforms | 13 | | |

Pin Configurations

Figure 1. 100-pin TQFP (14 × 20 × 1.4 mm) pinout [1]



Note

1. **Errata:** The ZZ pin (Pin 64) needs to be externally connected to ground. For more information, see "Errata" on page 22.

Pin Definitions

| Name | I/O | Description |
|---|--------------------|---|
| A ₀ , A ₁ , A | Input-Synchronous | Address Inputs Used to Select One of the 128 K Address Locations. Sampled at the rising edge of the CLK if ADSP or ADSC is active LOW, and \overline{CE}_1 , CE_2 , and \overline{CE}_3 are sampled active. A _[1:0] feeds the 2-bit counter. |
| \overline{BW}_A , \overline{BW}_B , \overline{BW}_C , \overline{BW}_D | Input-Synchronous | Byte Write Select Inputs, Active LOW. Qualified with \overline{BWE} to conduct byte writes to the SRAM. Sampled on the rising edge of CLK. |
| \overline{GW} | Input-Synchronous | Global Write Enable Input, Active LOW. When asserted LOW on the rising edge of CLK, a global write is conducted (ALL bytes are written, regardless of the values on $BW_{[A:D]}$ and \overline{BWE}). |
| \overline{BWE} | Input-Synchronous | Byte Write Enable Input, Active LOW. Sampled on the rising edge of CLK. This signal must be asserted LOW to conduct a byte write. |
| CLK | Input-Clock | Clock Input. Used to capture all synchronous inputs to the device. Also used to increment the burst counter when ADV is asserted LOW, during a burst operation. |
| \overline{CE}_1 | Input-Synchronous | Chip Enable 1 Input, Active LOW. Sampled on the rising edge of CLK. Used in conjunction with CE_2 and \overline{CE}_3 to select or deselect the device. ADSP is ignored if \overline{CE}_1 is HIGH. \overline{CE}_1 is sampled only when a new external address is loaded. |
| CE_2 | Input-Synchronous | Chip Enable 2 Input, Active HIGH. Sampled on the rising edge of CLK. Used in conjunction with \overline{CE}_1 and \overline{CE}_3 to select or deselect the device. CE_2 is sampled only when a new external address is loaded. |
| \overline{CE}_3 | Input-Synchronous | Chip Enable 3 Input, Active LOW. Sampled on the rising edge of CLK. Used in conjunction with \overline{CE}_1 and CE_2 to select or deselect the device. \overline{CE}_3 is sampled only when a new external address is loaded. |
| OE | Input-Asynchronous | Output Enable, Asynchronous Input, Active LOW. Controls the direction of the I/O pins. When LOW, the I/O pins behave as outputs. When deasserted HIGH, I/O pins are tristated, and act as input data pins. OE is masked during the first clock of a read cycle when emerging from a deselected state. |
| ADV | Input-Synchronous | Advance Input Signal, Sampled on the Rising Edge of CLK. When asserted, it automatically increments the address in a burst cycle. |
| ADSP | Input-Synchronous | Address Strobe from Processor, Sampled on the Rising Edge of CLK. When asserted LOW, addresses presented to the device are captured in the address registers. A _[1:0] are also loaded into the burst counter. When ADSP and ADSC are both asserted, only ADSP is recognized. ADSP is ignored when \overline{CE}_1 is deasserted HIGH. |
| ADSC | Input-Synchronous | Address Strobe from Controller, Sampled on the Rising Edge of CLK. When asserted LOW, addresses presented to the device are captured in the address registers. A _[1:0] are also loaded into the burst counter. When ADSP and ADSC are both asserted, only ADSP is recognized. |

Pin Definitions (continued)

| Name | I/O | Description |
|---|--------------------|--|
| ZZ ^[2] | Input-Asynchronous | ZZ “Sleep” Input. This active HIGH input places the device in a non-time-critical “sleep” condition with data integrity preserved. During normal operation, this pin must be LOW or left floating. ZZ pin has an internal pull-down. |
| DQ _A , DQ _B , DQ _C , DQ _D , DQP _A , DQP _B , DQP _C , DQP _D | I/O-Synchronous | Bidirectional Data I/O Lines. As inputs, they feed into an on-chip data register that is triggered by the rising edge of CLK. As outputs, they deliver the data contained in the memory location specified by the addresses presented during the previous clock rise of the read cycle. The direction of the pins is controlled by OE. When OE is asserted LOW, the pins behave as outputs. When HIGH, DQs and DQPs are placed in a tristate condition. |
| V _{DD} | Power Supply | Power Supply Inputs to the Core of the Device. |
| V _{SS} | Ground | Ground for the Core of the Device. |
| V _{DDQ} | I/O Power Supply | Power Supply for the I/O circuitry. |
| V _{SSQ} | I/O Ground | Ground for the I/O circuitry. |
| MODE | Input-Static | Selects Burst Order. When tied to GND selects linear burst sequence. When tied to V _{DDQ} or left floating selects interleaved burst sequence. This is a strap pin and must remain static during device operation. Mode pin has an internal pull-up. |
| NC, NC/9M, NC/18M, NC/36M, NC/72M, NC/144M, NC/288M, NC/576M, NC/1G | – | No Connects. Not internally connected to the die. NC/9M, NC/18M, NC/36M, NC/72M, NC/144M, NC/288M, NC/576M, and NC/1G are address expansion pins that are not internally connected to the die. |

Note

2. **Errata:** The ZZ pin needs to be externally connected to ground. For more information, see "Errata" on page 22.

Functional Overview

All synchronous inputs pass through input registers controlled by the rising edge of the clock. All data outputs pass through output registers controlled by the rising edge of the clock. Maximum access delay from the clock rise (t_{CO}) is 2.6 ns (250 MHz device).

The CY7C1347G supports secondary cache in systems using either a linear or interleaved burst sequence. The linear burst sequence is suited for processors that use a linear burst sequence. The burst order is user selectable, and is determined by sampling the MODE input. Accesses can be initiated with either the Address Strobe from Processor (ADSP) or the Address Strobe from Controller (ADSC). Address advancement through the burst sequence is controlled by the ADV input. A two-bit on-chip wraparound burst counter captures the first address in a burst sequence and automatically increments the address for the rest of the burst access.

Byte write operations are qualified with the Byte Write Enable (BWE) and Byte Write Select ($BW_{[A:D]}$) inputs. A Global Write Enable (GW) overrides all byte write inputs and writes data to all four bytes. All writes are simplified with on-chip synchronous self timed write circuitry.

Three synchronous Chip Selects (\overline{CE}_1 , CE_2 , \overline{CE}_3) and an asynchronous Output Enable (\overline{OE}) provide for easy bank selection and output tristate control. ADSP is ignored if CE_1 is HIGH.

Single Read Accesses

This access is initiated when the following conditions are satisfied at clock rise: (1) ADSP or ADSC is asserted LOW, (2) \overline{CE}_1 , CE_2 , CE_3 are all asserted active, and (3) the write signals (GW, BWE) are all deasserted HIGH. ADSP is ignored if CE_1 is HIGH. The address presented to the address inputs ($A_{[16:0]}$) is stored into the address advancement logic and the Address Register while being presented to the memory core. The corresponding data is allowed to propagate to the input of the Output Registers. At the rising edge of the next clock the data is allowed to propagate through the Output Register and onto the data bus within 2.6 ns (250 MHz device) if \overline{OE} is active LOW. The only exception occurs when the SRAM is emerging from a deselected state to a selected state, its outputs are always tristated during the first cycle of the access. After the first cycle of the access, the outputs are controlled by the \overline{OE} signal. Consecutive single read cycles are supported. After the SRAM is deselected at clock rise by the chip select and either ADSP or ADSC signals, its output tristates immediately.

Single Write Accesses Initiated by ADSP

This access is initiated when both of the following conditions are satisfied at clock rise: (1) ADSP is asserted LOW, and (2) \overline{CE}_1 , CE_2 , CE_3 are all asserted active. The address presented to $A_{[16:0]}$ is loaded into the Address Register and the address advancement logic while being delivered to the RAM core. The write signals (GW, BWE, and $BW_{[A:D]}$) and ADV inputs are ignored during this first cycle.

\overline{ADSP} -triggered write accesses require two clock cycles to complete. If GW is asserted LOW on the second clock rise, the data presented to the DQs and DQPs inputs is written into the corresponding address location in the RAM core. If \overline{GW} is HIGH, then the write operation is controlled by BWE and $BW_{[A:D]}$ signals. The CY7C1347G provides byte write capability that is described in "Partial Truth Table for Read/Write" on page 10. Asserting the Byte Write Enable input (BWE) with the selected Byte Write ($BW_{[A:D]}$) input selectively writes to only the desired bytes.

Bytes not selected during a byte write operation remain unaltered. A synchronous self timed write mechanism is provided to simplify the write operations.

Because the CY7C1347G is a common I/O device, the Output Enable (\overline{OE}) must be deasserted HIGH before presenting data to the DQs and DQPs inputs. Doing so tristates the output drivers. As a safety precaution, DQs and DQPs are automatically tristated whenever a write cycle is detected, regardless of the state of \overline{OE} .

Single Write Accesses Initiated by ADSC

\overline{ADSC} write accesses are initiated when the following conditions are satisfied: (1) ADSC is asserted LOW, (2) ADSP is deasserted HIGH, (3) CE_1 , CE_2 , CE_3 are all asserted active, and (4) the appropriate combination of the write inputs (GW, BWE, and $BW_{[A:D]}$) are asserted active to conduct a write to the desired byte(s). ADSC-triggered write accesses require a single clock cycle to complete. The address presented to $A_{[16:0]}$ is loaded into the address register and the address advancement logic while being delivered to the RAM core. The ADV input is ignored during this cycle. If a global write is conducted, the data presented to the DQs and DQPs is written into the corresponding address location in the RAM core. If a byte write is conducted, only the selected bytes are written. Bytes not selected during a byte write operation remain unaltered. A synchronous self timed write mechanism has been provided to simplify the write operations.

Because the CY7C1347G is a common I/O device, the Output Enable (\overline{OE}) must be deasserted HIGH before presenting data to the DQs and DQPs inputs. Doing so tristates the output drivers. As a safety precaution, DQs and DQPs are automatically tristated whenever a write cycle is detected, regardless of the state of \overline{OE} .

Burst Sequences

The CY7C1347G provides a two-bit wraparound counter, fed by $A_{[1:0]}$, that implements either an interleaved or linear burst sequence. The interleaved burst sequence is designed specifically to support Intel Pentium applications. The linear burst sequence is designed to support processors that follow a linear burst sequence. The burst sequence is user-selectable through the MODE input.

Asserting \overline{ADV} LOW at clock rise automatically increments the burst counter to the next address in the burst sequence. Both read and write burst operations are supported.

Sleep Mode

The ZZ input pin is an asynchronous input. Asserting ZZ places the SRAM in a power conservation “sleep” mode. Two clock cycles are required to enter into or exit from this “sleep” mode. While in this mode, data integrity is guaranteed. Accesses pending when entering the “sleep” mode are not considered valid nor is the completion of the operation guaranteed. The device must be deselected before entering the “sleep” mode. CE₁, CE₂, CE₃, ADSP, and ADSC must remain inactive for the duration of t_{ZZREC} after the ZZ input returns LOW.

Interleaved Burst Sequence

| First Address A _[1:0] | Second Address A _[1:0] | Third Address A _[1:0] | Fourth Address A _[1:0] |
|-------------------------------------|--------------------------------------|-------------------------------------|--------------------------------------|
| 00 | 01 | 10 | 11 |
| 01 | 00 | 11 | 10 |
| 10 | 11 | 00 | 01 |
| 11 | 10 | 01 | 00 |

Linear Burst Sequence

| First Address A _[1:0] | Second Address A _[1:0] | Third Address A _[1:0] | Fourth Address A _[1:0] |
|-------------------------------------|--------------------------------------|-------------------------------------|--------------------------------------|
| 00 | 01 | 10 | 11 |
| 01 | 10 | 11 | 00 |
| 10 | 11 | 00 | 01 |
| 11 | 00 | 01 | 10 |

ZZ Mode Electrical Characteristics

| Parameter | Description | Test Conditions | Min | Max | Unit |
|--------------------|------------------------------------|------------------------------|-------------------|-------------------|------|
| I _{DDZZ} | Snooze mode standby current | ZZ ≥ V _{DD} - 0.2 V | – | 40 | mA |
| t _{ZZS} | Device operation to ZZ | ZZ ≥ V _{DD} - 0.2 V | – | 2t _{CYC} | ns |
| t _{ZZREC} | ZZ recovery time | ZZ ≤ 0.2 V | 2t _{CYC} | – | ns |
| t _{ZZI} | ZZ Active to snooze current | This parameter is sampled | – | 2t _{CYC} | ns |
| t _{RZZI} | ZZ Inactive to exit snooze current | This parameter is sampled | 0 | – | ns |

Truth Table

The truth table for part number CY7C1347G follow.

| Next Cycle ^[3, 4, 5, 6, 7] | Add. Used | \overline{CE}_1 | CE_2 | \overline{CE}_3 | ZZ | \overline{ADSP} | \overline{ADSC} | \overline{ADV} | \overline{WRITE} | \overline{OE} | CLK | DQ |
|---------------------------------------|-----------|-------------------|--------|-------------------|----|-------------------|-------------------|------------------|--------------------|-----------------|-----|----------|
| Deselect cycle, power-down | None | H | X | X | L | X | L | X | X | X | L-H | Tristate |
| Deselect cycle, power-down | None | L | L | X | L | L | X | X | X | X | L-H | Tristate |
| Deselect cycle, power-down | None | L | X | H | L | L | X | X | X | X | L-H | Tristate |
| Deselect cycle, power-down | None | L | L | X | L | H | L | X | X | X | L-H | Tristate |
| Deselect cycle, power-down | None | L | X | H | L | H | L | X | X | X | L-H | Tristate |
| Snooze mode, power-down | None | X | X | X | H | X | X | X | X | X | X | Tristate |
| Read Cycle, Begin Burst | External | L | H | L | L | L | X | X | X | L | L-H | Q |
| Read Cycle, Begin Burst | External | L | H | L | L | L | X | X | X | H | L-H | Tristate |
| Write Cycle, Begin Burst | External | L | H | L | L | H | L | X | L | X | L-H | D |
| Read Cycle, Begin Burst | External | L | H | L | L | H | L | X | H | L | L-H | Q |
| Read Cycle, Begin Burst | External | L | H | L | L | H | L | X | H | H | L-H | Tristate |
| Read Cycle, Continue Burst | Next | X | X | X | L | H | H | L | H | H | L-H | Tristate |
| Read Cycle, Continue Burst | Next | X | X | X | L | H | H | L | H | L | L-H | Q |
| Read Cycle, Continue Burst | Next | H | X | X | L | X | H | L | H | L | L-H | Q |
| Read Cycle, Continue Burst | Next | H | X | X | L | X | H | L | H | H | L-H | Tristate |
| Write cycle, continue burst | Next | X | X | X | L | H | H | L | L | X | L-H | D |
| Write cycle, continue burst | Next | H | X | X | L | X | H | L | L | X | L-H | D |
| Read cycle, suspend burst | Current | X | X | X | L | H | H | H | H | L | L-H | Q |
| Read cycle, suspend burst | Current | X | X | X | L | H | H | H | H | H | L-H | Tristate |
| Read cycle, suspend burst | Current | H | X | X | L | X | H | H | H | L | L-H | Q |
| Read cycle, suspend burst | Current | H | X | X | L | X | H | H | H | H | L-H | Tristate |
| Write cycle, suspend burst | Current | X | X | X | L | H | H | H | L | X | L-H | D |
| Write cycle, suspend burst | Current | H | X | X | L | X | H | H | L | X | L-H | D |

Notes

- X = "Do not Care." H = Logic HIGH, L = Logic LOW.
- $\overline{WRITE} = L$ when any one or more Byte Write Enable signals ($\overline{BW}_A, \overline{BW}_B, \overline{BW}_C, \overline{BW}_D$) and $\overline{BWE} = L$ or $\overline{GW} = L$. $\overline{WRITE} = H$ when all Byte Write Enable signals ($\overline{BW}_A, \overline{BW}_B, \overline{BW}_C, \overline{BW}_D$), \overline{BWE} , $\overline{GW} = H$.
- The DQ pins are controlled by the current cycle and the \overline{OE} signal. \overline{OE} is asynchronous and is not sampled with the clock.
- The SRAM always initiates a read cycle when \overline{ADSP} is asserted, regardless of the state of \overline{GW} , \overline{BWE} , or $\overline{BW}_{[A,D]}$. Writes may occur only on subsequent clocks after the \overline{ADSP} or with the assertion of \overline{ADSC} . As a result, \overline{OE} must be driven HIGH before the start of the write cycle to allow the outputs to tristate. \overline{OE} is a do not care for the remainder of the write cycle.
- \overline{OE} is asynchronous and is not sampled with the clock rise. It is masked internally during write cycles. During a read cycle all data bits are tristate when \overline{OE} is inactive or when the device is deselected, and all data bits behave as output when \overline{OE} is active (LOW).

Partial Truth Table for Read/Write

The partial truth table for read/write for part number CY7C1347G follow.

| Function ^[8, 9] | \overline{GW} | \overline{BWE} | \overline{BW}_D | \overline{BW}_C | \overline{BW}_B | \overline{BW}_A |
|--------------------------------|-----------------|------------------|-------------------|-------------------|-------------------|-------------------|
| Read | H | H | X | X | X | X |
| Read | H | L | H | H | H | H |
| Write byte A – DQ _A | H | L | H | H | H | L |
| Write byte B – DQ _B | H | L | H | H | L | H |
| Write bytes B, A | H | L | H | H | L | L |
| Write byte C – DQ _C | H | L | H | L | H | H |
| Write bytes C, A | H | L | H | L | H | L |
| Write bytes C, B | H | L | H | L | L | H |
| Write bytes C, B, A | H | L | H | L | L | L |
| Write byte D – DQ _D | H | L | L | H | H | H |
| Write bytes D, A | H | L | L | H | H | L |
| Write bytes D, B | H | L | L | H | L | H |
| Write bytes D, B, A | H | L | L | H | L | L |
| Write bytes D, C | H | L | L | L | H | H |
| Write bytes D, C, A | H | L | L | L | H | L |
| Write bytes D, C, B | H | L | L | L | L | H |
| Write all bytes | H | L | L | L | L | L |
| Write all bytes | L | X | X | X | X | X |

Notes

8. X = "Do not Care." H = Logic HIGH, L = Logic LOW.

9. This table is only a partial listing of the byte write combinations. Any combination of \overline{BW}_x is valid. Appropriate write is based on which byte write is active.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

| | |
|--|-----------------------------------|
| Storage temperature | -65 °C to +150 °C |
| Ambient temperature with power applied | -55 °C to +125 °C |
| Supply voltage on V _{DD} relative to GND | -0.5 V to +4.6 V |
| Supply voltage on V _{DDQ} relative to GND | -0.5 V to +V _{DD} |
| DC voltage applied to outputs in high Z State | -0.5 V to V _{DD} + 0.5 V |
| DC input voltage | -0.5 V to V _{DD} + 0.5 V |
| Current into outputs (LOW) | 20 mA |
| Static discharge voltage (MIL-STD-883, Method 3015) | > 2001 V |
| Latch-up Current | > 200 mA |

Operating Range

| Range | Ambient Temperature | V _{DD} | V _{DDQ} |
|------------|---------------------|-------------------|-------------------------------|
| Commercial | 0 °C to +70 °C | 3.3 V – 5% / +10% | 2.5 V – 5% to V _{DD} |
| Industrial | -40 °C to +85 °C | | |

Neutron Soft Error Immunity

| Parameter | Description | Test Conditions | Typ | Max* | Unit |
|-----------|---------------------------|-----------------|-----|------|---------|
| LSBU | Logical single-bit upsets | 25 °C | 361 | 394 | FIT/Mb |
| LMBU | Logical multi-bit upsets | 25 °C | 0 | 0.01 | FIT/Mb |
| SEL | Single event latch-up | 85 °C | 0 | 0.1 | FIT/Dev |

* No LMBU or SEL events occurred during testing; this column represents a statistical χ^2 , 95% confidence limit calculation. For more details refer to Application Note, Accelerated Neutron SER Testing and Calculation of Terrestrial Failure Rates – AN54908.

Electrical Characteristics

Over the Operating Range

| Parameter ^[10, 11] | Description | Test Conditions | Min | Max | Unit |
|-------------------------------|--|---|-------|-----------------------|------|
| V _{DD} | Power supply voltage | | 3.135 | 3.6 | V |
| V _{DDQ} | I/O supply voltage | | 2.375 | V _{DD} | V |
| V _{OH} | Output HIGH voltage | For 3.3 V I/O, I _{OH} = -4.0 mA | 2.4 | – | V |
| | | For 2.5 V I/O, I _{OH} = -1.0 mA | 2.0 | – | V |
| V _{OL} | Output LOW voltage | For 3.3 V I/O, I _{OL} = 8.0 mA | – | 0.4 | V |
| | | For 2.5 V I/O, I _{OL} = 1.0 mA | – | 0.4 | V |
| V _{IH} | Input HIGH voltage ^[10] | For 3.3 V I/O | 2.0 | V _{DD} + 0.3 | V |
| | | For 2.5 V I/O | 1.7 | V _{DD} + 0.3 | V |
| V _{IL} | Input LOW voltage ^[10] | For 3.3 V I/O | -0.3 | 0.8 | V |
| | | For 2.5 V I/O | -0.3 | 0.7 | V |
| I _X | Input leakage current except ZZ and MODE | GND ≤ V _I ≤ V _{DDQ} | -5 | 5 | μA |
| | Input current of MODE | Input = V _{SS} | -30 | – | μA |
| | | Input = V _{DD} | – | 5 | μA |
| | Input current of ZZ | Input = V _{SS} | -5 | – | μA |
| Input = V _{DD} | | – | 30 | μA | |
| I _{OZ} | Output leakage current | GND ≤ V _I ≤ V _{DDQ} , output disabled | -5 | 5 | μA |

Notes

10. Overshoot: V_{IH(AC)} < V_{DD} + 1.5 V (pulse width less than t_{CYC/2}). Undershoot: V_{IL(AC)} > -2 V (pulse width less than t_{CYC/2}).
 11. t_{power-up}: assumes a linear ramp from 0 V to V_{DD(min)} within 200 ms. During this time V_{IH} < V_{DD} and V_{DDQ} ≤ V_{DD}.

Electrical Characteristics (continued)

Over the Operating Range

| Parameter ^[10, 11] | Description | Test Conditions | Min | Max | Unit | |
|-------------------------------|--|---|--------------------------|-----|------|----|
| I _{DD} | V _{DD} operating supply current | V _{DD} = Max., I _{OUT} = 0 mA, f = f _{MAX} = 1/t _{CYC} | 4 ns cycle, 250 MHz | – | 325 | mA |
| | | | 5 ns cycle, 200 MHz | – | 265 | mA |
| | | | 6 ns cycle, 166 MHz | – | 240 | mA |
| | | | 7.5 ns cycle, 133 MHz | – | 225 | mA |
| I _{SB1} | Automatic CE power-down current – TTL inputs | Max. V _{DD} , device deselected, V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX} = 1/t _{CYC} | 4 ns cycle, 250 MHz | – | 120 | mA |
| | | | 5 ns cycle, 200 MHz | – | 110 | mA |
| | | | 6 ns cycle, 166 MHz | – | 100 | mA |
| | | | 7.5 ns cycle, 133 MHz | – | 90 | mA |
| I _{SB2} | Automatic CE power-down current – CMOS inputs | Max. V _{DD} , device deselected, V _{IN} ≤ 0.3 V or V _{IN} ≥ V _{DDQ} – 0.3 V, f = 0 | All speeds | – | 40 | mA |
| I _{SB3} | Automatic CE power-down current – CMOS inputs | Max. V _{DD} , device deselected, V _{IN} ≤ 0.3 V or V _{IN} ≥ V _{DDQ} – 0.3 V, f = f _{MAX} = 1/t _{CYC} | 4 ns cycle, 250 MHz | – | 105 | mA |
| | | | 5 ns cycle, 200 MHz | – | 95 | mA |
| | | | 6 ns cycle, 166 MHz | – | 85 | mA |
| | | | 7.5 ns cycle, 133 MHz | – | 75 | mA |
| I _{SB4} | Automatic CE power-down current – TTL inputs | Max. V _{DD} , device deselected, V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = 0 | | – | 45 | mA |

Capacitance

| Parameter ^[12] | Description | Test Conditions | 100-pin TQFP Max | Unit |
|---------------------------|-------------------------|---|------------------|------|
| C _{IN} | Input capacitance | T _A = 25 °C, f = 1 MHz, V _{DD} = 3.3 V, V _{DDQ} = 3.3 V | 5 | pF |
| C _{CLK} | Clock input capacitance | | 5 | pF |
| C _{IO} | I/O capacitance | | 5 | pF |

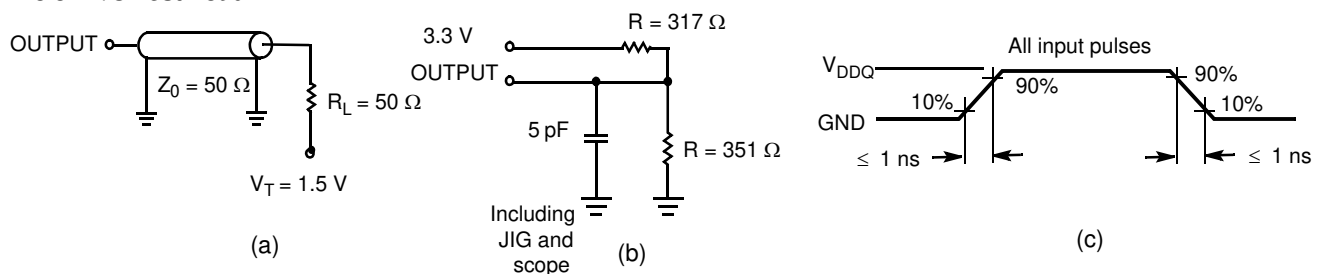
Thermal Resistance

| Parameter ^[12] | Description | Test Conditions | 100-pin TQFP Package | Unit |
|---------------------------|--|--|----------------------|------|
| Θ _{JA} | Thermal resistance (junction to ambient) | Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51. | 30.32 | °C/W |
| Θ _{JC} | Thermal resistance (junction to case) | | 6.85 | °C/W |

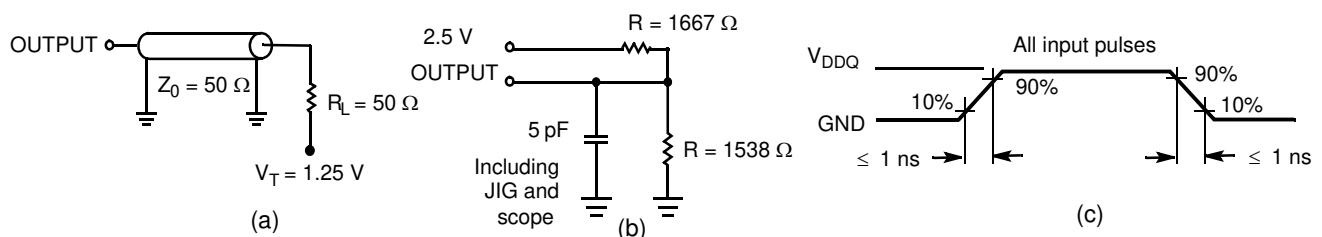
AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms

3.3 V I/O Test Load



2.5 V I/O Test Load



Note

12. Tested initially and after any design or process changes that may affect these parameters.

Switching Characteristics

Over the Operating Range

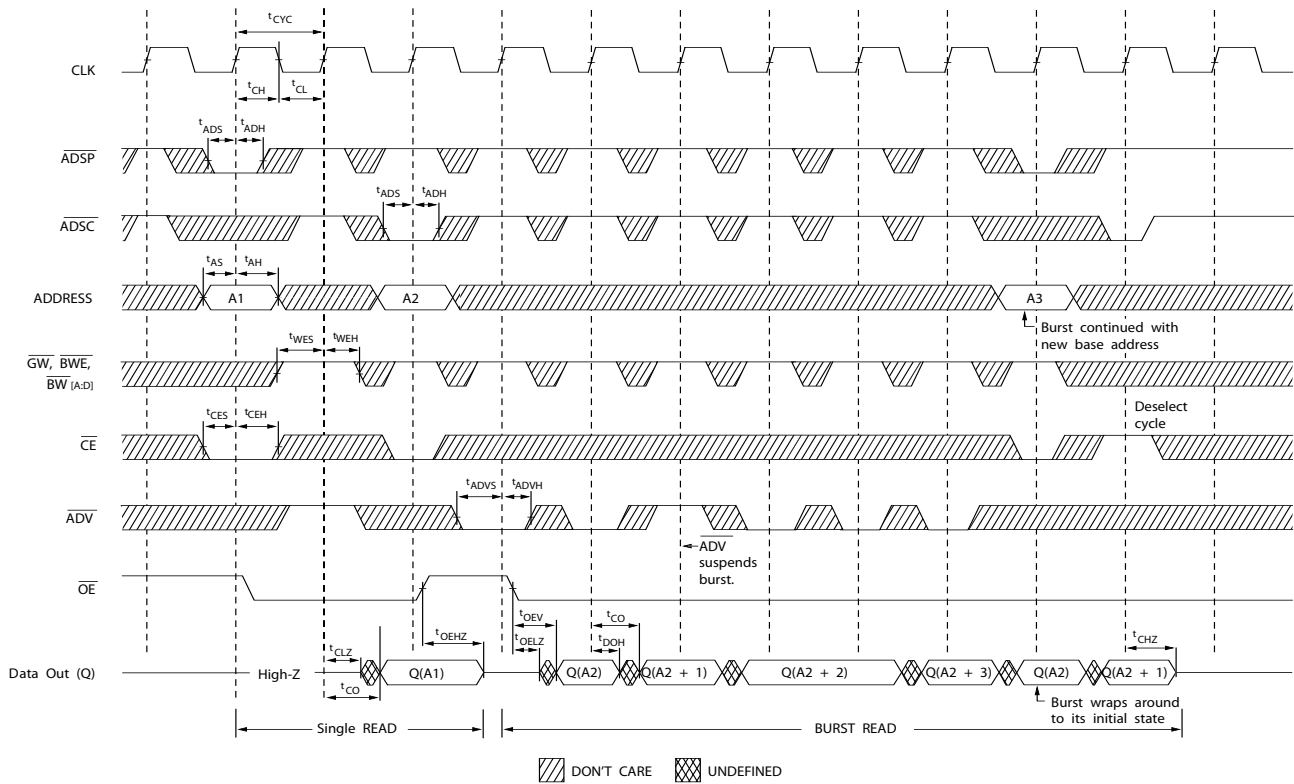
| Parameter [13, 14] | Description | -250 | | -200 | | -166 | | -133 | | Unit |
|---------------------|--|------|-----|------|-----|------|-----|------|-----|------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | |
| t _{POWER} | V _{DD} (typical) to the first access [15] | 1 | – | 1 | – | 1 | – | 1 | – | ms |
| Clock | | | | | | | | | | |
| t _{CYC} | Clock cycle time | 4.0 | – | 5.0 | – | 6.0 | – | 7.5 | – | ns |
| t _{CH} | Clock HIGH | 1.7 | – | 2.0 | – | 2.5 | – | 3.0 | – | ns |
| t _{CL} | Clock LOW | 1.7 | – | 2.0 | – | 2.5 | – | 3.0 | – | ns |
| Output Times | | | | | | | | | | |
| t _{CO} | Data output valid after CLK rise | – | 2.6 | – | 2.8 | – | 3.5 | – | 4.0 | ns |
| t _{DOH} | Data output hold after CLK rise | 1.0 | – | 1.0 | – | 1.5 | – | 1.5 | – | ns |
| t _{CLZ} | Clock to low Z [16, 17, 18] | 0 | – | 0 | – | 0 | – | 0 | – | ns |
| t _{CHZ} | Clock to high Z [16, 17, 18] | – | 2.6 | – | 2.8 | – | 3.5 | – | 4.0 | ns |
| t _{OEV} | \overline{OE} LOW to output valid | – | 2.6 | – | 2.8 | – | 3.5 | – | 4.5 | ns |
| t _{OELZ} | \overline{OE} LOW to output low Z [16, 17, 18] | 0 | – | 0 | – | 0 | – | 0 | – | ns |
| t _{OEHZ} | \overline{OE} HIGH to output high Z [16, 17, 18] | – | 2.6 | – | 2.8 | – | 3.5 | – | 4.0 | ns |
| Setup Times | | | | | | | | | | |
| t _{AS} | Address setup before CLK rise | 1.2 | – | 1.2 | – | 1.5 | – | 1.5 | – | ns |
| t _{ADS} | \overline{ADSC} , \overline{ADSP} setup before CLK rise | 1.2 | – | 1.2 | – | 1.5 | – | 1.5 | – | ns |
| t _{ADVS} | \overline{ADV} setup before CLK rise | 1.2 | – | 1.2 | – | 1.5 | – | 1.5 | – | ns |
| t _{WES} | \overline{GW} , \overline{BWE} , \overline{BW}_X setup before CLK rise | 1.2 | – | 1.2 | – | 1.5 | – | 1.5 | – | ns |
| t _{DS} | Data input setup before CLK rise | 1.2 | – | 1.2 | – | 1.5 | – | 1.5 | – | ns |
| t _{CES} | Chip enable setup before CLK rise | 1.2 | – | 1.2 | – | 1.5 | – | 1.5 | – | ns |
| Hold Times | | | | | | | | | | |
| t _{AH} | Address hold after CLK rise | 0.3 | – | 0.5 | – | 0.5 | – | 0.5 | – | ns |
| t _{ADH} | \overline{ADSP} , \overline{ADSC} hold after CLK rise | 0.3 | – | 0.5 | – | 0.5 | – | 0.5 | – | ns |
| t _{ADVH} | \overline{ADV} hold after CLK Rise | 0.3 | – | 0.5 | – | 0.5 | – | 0.5 | – | ns |
| t _{WEH} | \overline{GW} , \overline{BWE} , \overline{BW}_X hold after CLK rise | 0.3 | – | 0.5 | – | 0.5 | – | 0.5 | – | ns |
| t _{DH} | Data input hold after CLK rise | 0.3 | – | 0.5 | – | 0.5 | – | 0.5 | – | ns |
| t _{CEH} | Chip enable hold after CLK rise | 0.3 | – | 0.5 | – | 0.5 | – | 0.5 | – | ns |

Notes

13. Timing references level is 1.5 V when V_{DDQ} = 3.3 V and is 1.25 V when V_{DDQ} = 2.5 V on all datasheets.
14. Test conditions shown in (a) of Figure 2 on page 13 unless otherwise noted.
15. This part has an internal voltage regulator; t_{POWER} is the time that the power must be supplied above V_{DD(min)} initially before a read or write operation can be initiated.
16. t_{CHZ}, t_{CLZ}, t_{OELZ}, and t_{OEHZ} are specified with AC test conditions shown in part (b) of Figure 2 on page 13. Transition is measured ±200 mV from steady-state voltage.
17. At any voltage and temperature, t_{OEHZ} is less than t_{OELZ} and t_{CHZ} is less than t_{CLZ} to eliminate bus contention between SRAMs when sharing the same data bus. These specifications do not imply a bus contention condition, but reflect parameters guaranteed over worst case user conditions. Device is designed to achieve High Z before Low Z under the same system conditions.
18. This parameter is sampled and not 100% tested.

Switching Waveforms

Figure 3. Read Cycle Timing [19]

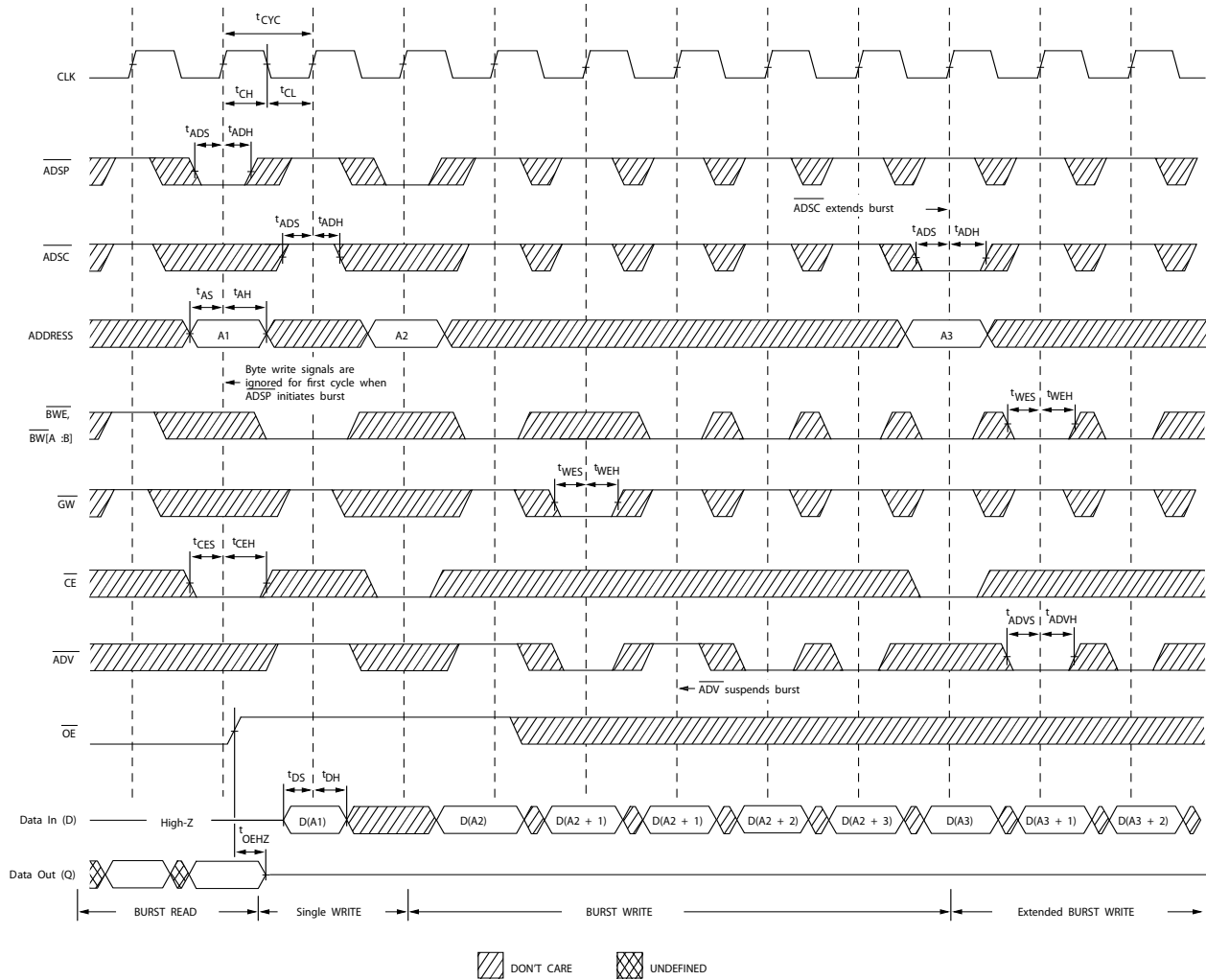


Note

19. In this diagram, when \overline{CE} is LOW, \overline{CE}_1 is LOW, CE_2 is HIGH, and \overline{CE}_3 is LOW. When \overline{CE} is HIGH, \overline{CE}_1 is HIGH, CE_2 is LOW, or \overline{CE}_3 is HIGH.

Switching Waveforms (continued)

Figure 4. Write Cycle Timing [20, 21]

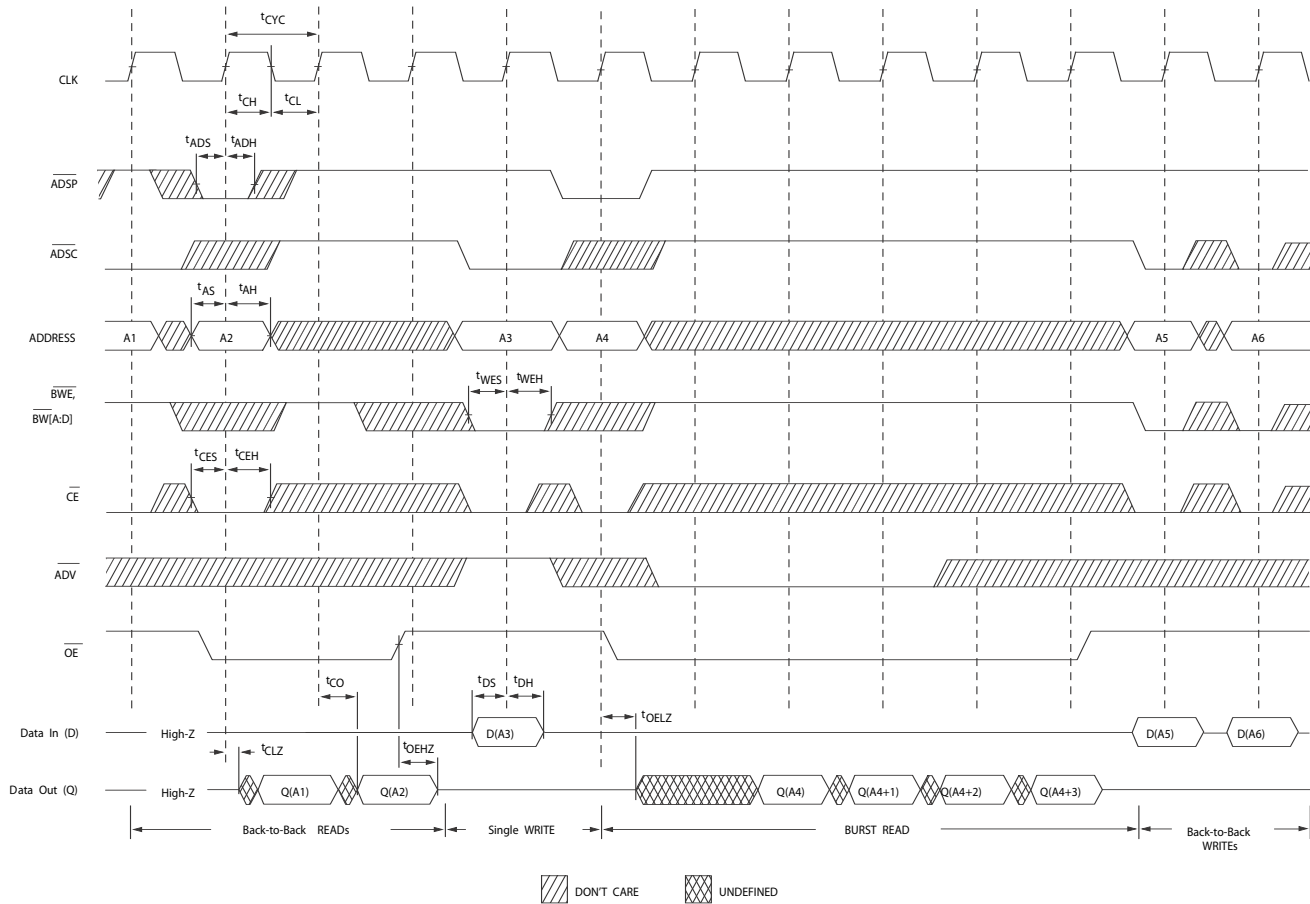


Notes

- 20. In this diagram, when \overline{CE} is LOW, \overline{CE}_1 is LOW, CE_2 is HIGH, and \overline{CE}_3 is LOW. When \overline{CE} is HIGH, \overline{CE}_1 is HIGH, CE_2 is LOW, or \overline{CE}_3 is HIGH.
- 21. Full width write can be initiated by either \overline{GW} LOW, or by \overline{GW} HIGH, \overline{BWE} LOW, and BW_x LOW.

Switching Waveforms (continued)

Figure 5. Read/Write Cycle Timing [22, 23, 24]

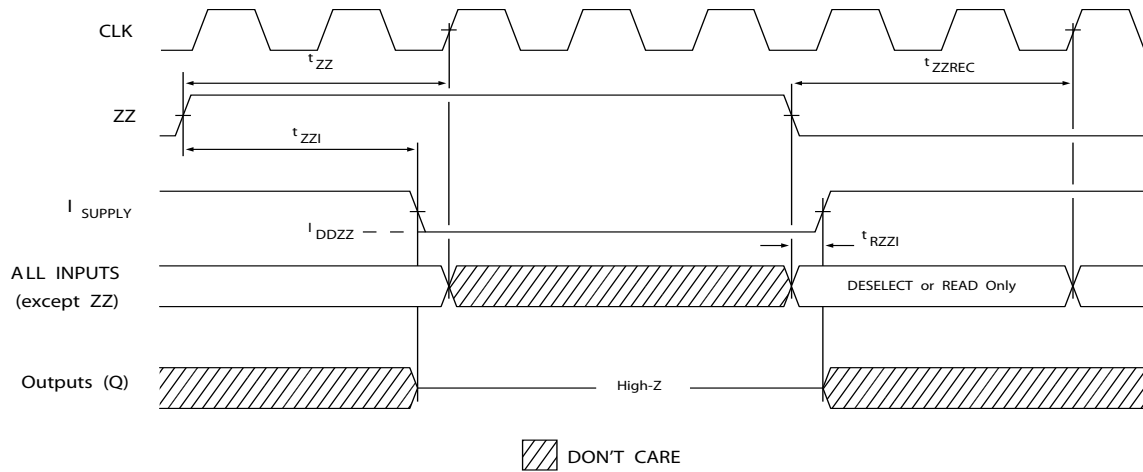


Notes

- 22. In this diagram, when \overline{CE} is LOW, \overline{CE}_1 is LOW, CE_2 is HIGH, and \overline{CE}_3 is LOW. When \overline{CE} is HIGH, \overline{CE}_1 is HIGH, CE_2 is LOW, or \overline{CE}_3 is HIGH.
- 23. The data bus (Q) remains in High Z following a write cycle, unless a new read access is initiated by \overline{ADSP} or \overline{ADSC} .
- 24. \overline{GW} is HIGH.

Switching Waveforms (continued)

Figure 6. ZZ Mode Timing [25, 26]



Notes

- 25. Device must be deselected when entering ZZ mode. See "Truth Table" on page 9 for all possible signal conditions to deselect the device.
- 26. DQs are in High Z when exiting ZZ sleep mode.

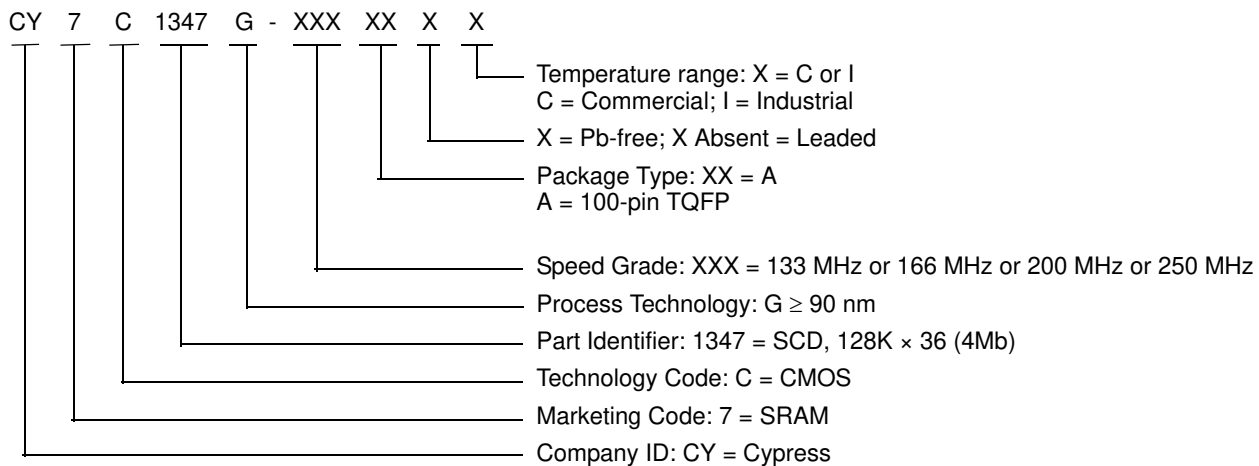
Ordering Information

The table below contains only the parts that are currently available. If you don't see what you are looking for, please contact your local sales representative. For more information, visit the Cypress website at www.cypress.com and refer to the product summary page at <http://www.cypress.com/products>

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives and distributors. To find the office closest to you, visit us at <http://www.cypress.com/go/datasheet/offices>

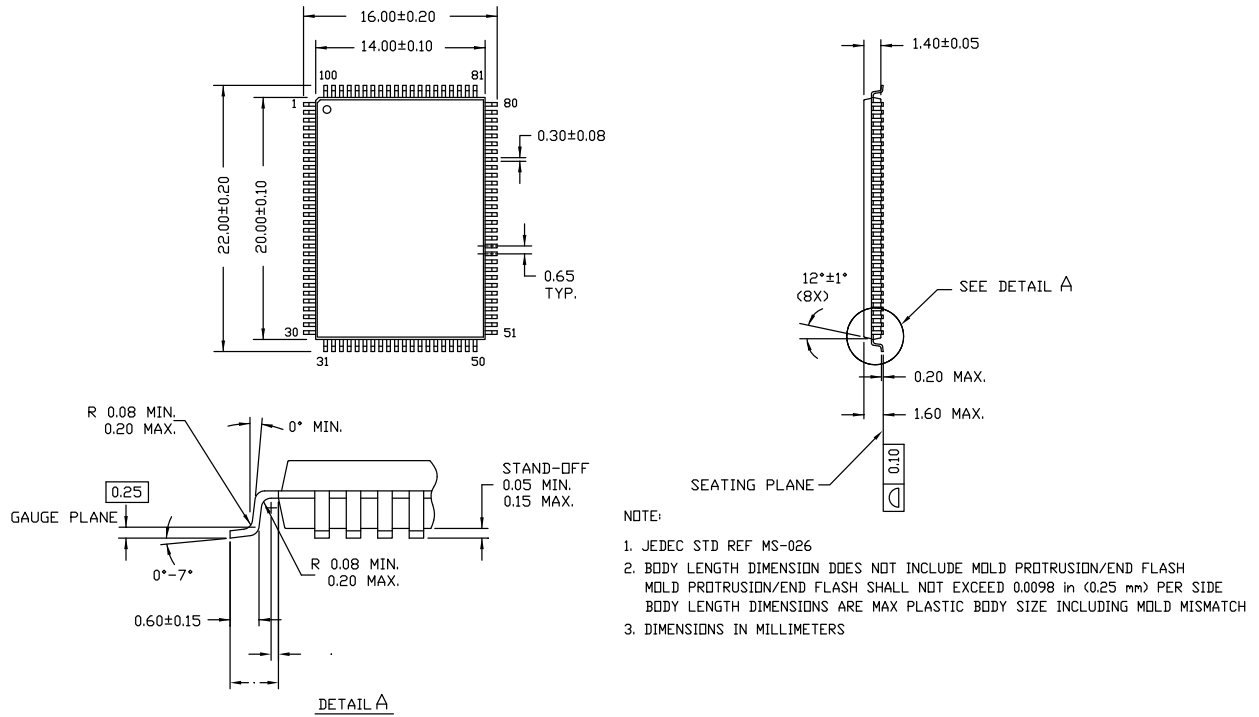
| Speed (MHz) | Ordering Code | Package Diagram | Package Type | Operating Range |
|-------------|------------------|-----------------|---|-----------------|
| 133 | CY7C1347G-133AXC | 51-85050 | 100-pin TQFP (14 × 20 × 1.4 mm) Pb-free | Commercial |
| | CY7C1347G-133AXI | 51-85050 | 100-pin TQFP (14 × 20 × 1.4 mm) Pb-free | Industrial |
| 166 | CY7C1347G-166AXC | 51-85050 | 100-pin TQFP (14 × 20 × 1.4 mm) Pb-free | Commercial |
| 200 | CY7C1347G-200AXC | 51-85050 | 100-pin TQFP (14 × 20 × 1.4 mm) Pb-free | Commercial |
| 250 | CY7C1347G-250AXC | 51-85050 | 100-pin TQFP (14 × 20 × 1.4 mm) Pb-free | Commercial |

Ordering Code Definitions



Package Diagrams

Figure 7. 100-pin TQFP (14 × 20 × 1.4 mm) A100RA Package Outline, 51-85050



51-85050 *E

Acronyms

| Acronym | Description |
|-----------------|---|
| \overline{CE} | Chip Enable |
| CMOS | Complementary Metal Oxide Semiconductor |
| I/O | Input/Output |
| JEDEC | Joint Electron Device Engineering Council |
| LMBU | Logical Multi-Bit Upsets |
| LSBU | Logical Single-Bit Upsets |
| \overline{OE} | Output Enable |
| SEL | Single Event Latch-up |
| SRAM | Static Random Access Memory |
| TQFP | Thin Quad Flat Pack |
| TTL | Transistor-Transistor Logic |
| \overline{WE} | Write Enable |

Document Conventions

Units of Measure

| Symbol | Unit of Measure |
|------------|-----------------|
| °C | degree Celsius |
| k Ω | kilohm |
| MHz | megahertz |
| μ A | microampere |
| μ s | microsecond |
| mA | milliampere |
| mV | millivolt |
| mm | millimeter |
| ms | millisecond |
| ns | nanosecond |
| Ω | ohm |
| % | percent |
| pF | picofarad |
| ps | picosecond |
| V | volt |
| W | watt |

Errata

This section describes the Ram9 Sync ZZ pin issue. Details include trigger conditions, the devices affected, proposed workaround and silicon revision applicability. Please contact your local Cypress sales representative if you have further questions.

Part Numbers Affected

| Density & Revision | Package Type | Operating Range |
|---------------------------------------|--------------|---------------------------|
| 4Mb-Ram9 Synchronous SRAMs: CY7C134*G | 100-pin TQFP | Commercial and Industrial |

Product Status

All of the devices in the Ram9 4Mb Sync family are qualified and available in production quantities.

Ram9 Sync ZZ Pin Issues Errata Summary

The following table defines the errata applicable to available Ram9 4Mb Sync family devices.

| Item | Issues | Description | Device | Fix Status |
|------|--------|--|----------------|--|
| 1. | ZZ Pin | When asserted HIGH, the ZZ pin places device in a "sleep" condition with data integrity preserved. The ZZ pin currently does not have an internal pull-down resistor and hence cannot be left floating externally by the user during normal mode of operation. | 4M-Ram9 (90nm) | For the 4M Ram9 (90 nm) devices, there is no plan to fix this issue. |

1. ZZ Pin Issue

■ Problem Definition

The problem occurs only when the device is operated in the normal mode with ZZ pin left floating. The ZZ pin on the SRAM device does not have an internal pull-down resistor. Switching noise in the system may cause the SRAM to recognize a HIGH on the ZZ input, which may cause the SRAM to enter sleep mode. This could result in incorrect or undesirable operation of the SRAM.

■ Trigger Conditions

Device operated with ZZ pin left floating.

■ Scope of Impact

When the ZZ pin is left floating, the device delivers incorrect data.

■ Workaround

Tie the ZZ pin externally to ground.

■ Fix Status

For the 4M Ram9 (90 nm) devices, there is no plan to fix this issue.

Document History Page

| Document Title: CY7C1347G, 4-Mbit (128K × 36) Pipelined Sync SRAM Document Number: 38-05516 | | | | |
|--|---------|-----------------|-----------------|---|
| Revision | ECN | Orig. of Change | Submission Date | Description of Change |
| ** | 224364 | RKF | See ECN | New data sheet. |
| *A | 276690 | VBL | See ECN | Updated Ordering Information (Changed TQFP package to Pb-free TQFP package, added comment on the BG and BZ Pb-free package availability below the table). |
| *B | 333625 | SYT | See ECN | Updated Features (Removed 225 MHz and 100 MHz frequencies related information). Updated Selection Guide (Removed 225 MHz and 100 MHz frequencies related information). Updated Pin Configurations (Updated Address Expansion balls in the pinouts for 100-pin TQFP Package as per JEDEC standards). Updated Pin Definitions . Updated Electrical Characteristics (Updated test conditions for V_{OL} and V_{OH} parameters, removed 225 MHz and 100 MHz frequencies related information). Updated Switching Characteristics (Removed 225 MHz and 100 MHz frequencies related information). Updated Thermal Resistance (Replaced TBDs for Θ_{JA} and Θ_{JC} to their respective values). Updated Ordering Information (By shading and unshading MPNs as per availability, changed the package name for 100-pin TQFP from A100RA to A101 in Package Name column, removed comment on the availability of BG Pb-free package). |
| *C | 419256 | R XU | See ECN | Changed status from Preliminary to Final. Changed address of Cypress Semiconductor Corporation from “3901 North First Street” to “198 Champion Court”. Updated Truth Table (Swapped typo \overline{CE}_2 and \overline{CE}_3 in the column heading). Updated Electrical Characteristics (Changed “Input Load Current except ZZ and MODE” to “Input Leakage Current except ZZ and MODE”, updated Note 11 (Changed test condition from $V_{IH} \leq V_{DD}$ to $V_{IH} < V_{DD}$)). Updated Ordering Information (Updated part numbers, replaced Package Name column with Package Diagram in the Ordering Information table). Updated Package Diagrams . |
| *D | 480124 | VKN | See ECN | Updated Maximum Ratings (Added the Maximum Rating for Supply Voltage on V_{DDQ} Relative to GND). Updated Ordering Information (Updated part numbers). |
| *E | 1078184 | VKN | See ECN | Updated Switching Waveforms (Updated Figure 4). |
| *F | 2633279 | NXR / AESA | 01/15/09 | Updated Ordering Information (Updated part numbers). Updated to new template. |
| *G | 2756998 | VKN | 08/28/09 | Included Neutron Soft Error Immunity . Updated Ordering Information (By including parts that are available, and modified the disclaimer for the Ordering information). Updated Package Diagrams . |
| *H | 2998771 | NJY | 08/02/10 | Updated Package Diagrams . Updated to new template. |
| *I | 3208774 | NJY | 03/29/2011 | Updated Ordering Information (Updated part numbers) and added Ordering Code Definitions . Updated Package Diagrams . |
| *J | 3310077 | OSN | 07/12/2011 | Added Units of Measure . Updated to new template. |

Document History Page (continued)

| Document Title: CY7C1347G, 4-Mbit (128K x 36) Pipelined Sync SRAM Document Number: 38-05516 | | | | |
|--|---------|-----------------|-----------------|--|
| Revision | ECN | Orig. of Change | Submission Date | Description of Change |
| *K | 3587066 | NJY / PRIT | 05/10/2012 | Updated Features (Removed non Pb-free 119-ball BGA package and 165-ball FBGA package related information, removed Industrial Temperature related information). Updated Functional Description (Removed the Note “For best practice recommendations, refer to the Cypress application note, SRAM System Guidelines – AN1064. ” and its reference). Updated Pin Configurations (Removed 165-ball FBGA package related information). Updated Operating Range (Removed Industrial Temperature Range). Updated Capacitance (Removed 165-ball FBGA package related information). Updated Thermal Resistance (Removed 165-ball FBGA package related information). Updated Package Diagrams (Removed 165-ball FBGA package related information). |
| *L | 3690005 | PRIT | 07/24/2012 | No technical updates. Completing Sunset Review. |
| *M | 3980577 | PRIT | 05/02/2013 | Updated Package Diagrams : spec 51-85115 – Changed revision from *C to *D. Added Errata . |
| *N | 4039646 | PRIT | 06/25/2013 | Added Errata Footnotes. Updated to new template. Completing Sunset Review. |
| *O | 4149033 | PRIT | 10/07/2013 | Updated Errata . |
| *P | 4419265 | PRIT | 06/25/2014 | Included Industrial Temperature Range related information in all instances across the document. Updated Ordering Information (Updated part numbers). Updated Package Diagrams : spec 51-85050 – Changed revision from *D to *E. Completing Sunset Review. |
| *Q | 4569232 | PRIT | 11/14/2014 | Updated Functional Description : Added “For a complete list of related documentation, click here. ” at the end. |
| *R | 5376171 | PRIT | 07/27/2016 | Removed 119-ball BGA package related information in all instances across the document. Updated Ordering Information : Updated part numbers. Updated Package Diagrams : Removed spec 51-85115 *D. Updated to new template. Completing Sunset Review. |

Sales, Solutions, and Legal Information

Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at [Cypress Locations](#).

Products

| | |
|-------------------------------|--|
| ARM® Cortex® Microcontrollers | cypress.com/arm |
| Automotive | cypress.com/automotive |
| Clocks & Buffers | cypress.com/clocks |
| Interface | cypress.com/interface |
| Lighting & Power Control | cypress.com/powerpsoc |
| Memory | cypress.com/memory |
| PSoC | cypress.com/psoc |
| Touch Sensing | cypress.com/touch |
| USB Controllers | cypress.com/usb |
| Wireless/Rf | cypress.com/wireless |

PSoC® Solutions

[PSoC 1](#) | [PSoC 3](#) | [PSoC 4](#) | [PSoC 5LP](#)

Cypress Developer Community

[Forums](#) | [Projects](#) | [Video](#) | [Blogs](#) | [Training](#) | [Components](#)

Technical Support

cypress.com/support

© Cypress Semiconductor Corporation, 2004-2016. This document is the property of Cypress Semiconductor Corporation and its subsidiaries, including Spansion LLC ("Cypress"). This document, including any software or firmware included or referenced in this document ("Software"), is owned by Cypress under the intellectual property laws and treaties of the United States and other countries worldwide. Cypress reserves all rights under such laws and treaties and does not, except as specifically stated in this paragraph, grant any license under its patents, copyrights, trademarks, or other intellectual property rights. If the Software is not accompanied by a license agreement and you do not otherwise have a written agreement with Cypress governing the use of the Software, then Cypress hereby grants you a personal, non-exclusive, nontransferable license (without the right to sublicense) (1) under its copyright rights in the Software (a) for Software provided in source code form, to modify and reproduce the Software solely for use with Cypress hardware products, only internally within your organization, and (b) to distribute the Software in binary code form externally to end users (either directly or indirectly through resellers and distributors), solely for use on Cypress hardware product units, and (2) under those claims of Cypress's patents that are infringed by the Software (as provided by Cypress, unmodified) to make, use, distribute, and import the Software solely for use with Cypress hardware products. Any other use, reproduction, modification, translation, or compilation of the Software is prohibited.

TO THE EXTENT PERMITTED BY APPLICABLE LAW, CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS DOCUMENT OR ANY SOFTWARE OR ACCOMPANYING HARDWARE, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. To the extent permitted by applicable law, Cypress reserves the right to make changes to this document without further notice. Cypress does not assume any liability arising out of the application or use of any product or circuit described in this document. Any information provided in this document, including any sample design information or programming code, is provided only for reference purposes. It is the responsibility of the user of this document to properly design, program, and test the functionality and safety of any application made of this information and any resulting product. Cypress products are not designed, intended, or authorized for use as critical components in systems designed or intended for the operation of weapons, weapons systems, nuclear installations, life-support devices or systems, other medical devices or systems (including resuscitation equipment and surgical implants), pollution control or hazardous substances management, or other uses where the failure of the device or system could cause personal injury, death, or property damage ("Unintended Uses"). A critical component is any component of a device or system whose failure to perform can be reasonably expected to cause the failure of the device or system, or to affect its safety or effectiveness. Cypress is not liable, in whole or in part, and you shall and hereby do release Cypress from any claim, damage, or other liability arising from or related to all Unintended Uses of Cypress products. You shall indemnify and hold Cypress harmless from and against all claims, costs, damages, and other liabilities, including claims for personal injury or death, arising from or related to any Unintended Uses of Cypress products.

Cypress, the Cypress logo, Spansion, the Spansion logo, and combinations thereof, PSoC, CapSense, EZ-USB, F-RAM, and Traveo are trademarks or registered trademarks of Cypress in the United States and other countries. For a more complete list of Cypress trademarks, visit cypress.com. Other names and brands may be claimed as property of their respective owners.